

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: RAJARAM BHAT, et al

Examiner:

Serial No:

Group Art Unit:

Filed:

For: GROWTH OF DILUTE NITRIDE
COMPOUNDSINFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.56, 1.97 – 1.98Commissioner of Patents
Alexandria, VA 22313-1450

Dear Sir:

The Examiner's attention is hereby directed to the following reference(s) listed on the attached Form PTO-1449 for consideration in connection with the examination of the above-identified patent application. One copy of the non-US reference(s) is enclosed.

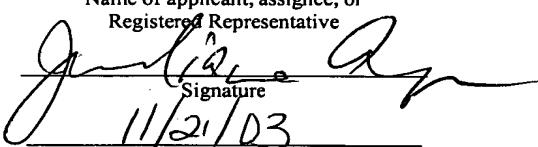
This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the enclosed documents constitute "prior art." If it should be determined that any of the submitted documents do not constitute "prior art" under United States law, applicant(s) reserve the right to present to the office the relevant facts and law regarding the appropriate status of such documents.

Applicant(s) further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the enclosed references, should one or more of the references be applied against the claims of the present application.

Respectfully submitted,


 Julianne Agon
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Date: 11/21/03

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner of Patents, Alexandria, Va 22313-1450 on	
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Julianne Agon	
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Signature	
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FORM PTO-1449 (MODIFIED)

ATTORNEY DOCKET NO.

SERIAL NO.

LIST OF PATENTS AND
PUBLICATIONS
FOR APPLICANTS INFORMATION
DISCLOSURE STATEMENT

SP03-165

APPLICANT RAJARAM BHAT, et al.

FILING DATE

GROUP:

REFERENCE DESIGNATION

U.S. PATENT and PUBLICATION DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date if Approp.
AA		2002/0085973A1	7/4/02	Park	423	351	
AB		5,689,123	11/18/97	Major, et al	257	190	
AC		5,891,790	4/6/99	Keller, et al	438	508	
AD		5,944,913	8/31/99	Hou	136	255	
AE		6,046,096	4/4/00	Ouchi	438	510	
AF		6,252,287	6/26/01	Kurtz, et al	257	461	
AG		6,342,405	1/29/02	Major, et al	438	46	
AH		6,358,822	3/19/02	Tomomura	438	483	
AI		6,596,079	7/22/03	Vaudo, et al	117	97	
AJ		6,645,885	11/11/03	Chua, et al	438	962	
AK							

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub-Class	Translation Yes No
	AL						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

AM	"Room Temperature Operation of GaInNAs/GaInP Double-Heterostructure Laser Diodes Grown by Metalorganic Chemical Vapor Deposition", Sato, et al Jpn. J. Appl. Phys. Vo. 36 1997 pp 2671-2675
AN	"Incorporation effects in MOCVD-grown (IN)GaAsN using different nitrogen precursors", Ptak, et al J. of Crystal Growth Vol. 243 (2002) 231-237
AO	"Red Shift of Photoluminescence and Absorption in Dilute GaAsN Alloy Layers", Weyers, et al Jpn. J. Appl. Phys. Vo. 31 1992 pp L853-L855
AP	"GaInNAs: A Novel Material for Long-Wavelength-Range Laser Diodes with Excellent high-Temperature Performance", Kondow, et al Jpn. J. Appl. Phys. Vo. 35 199 pp 1273-1275
AQ	"Gas-Source Molecular Beam Epitaxy of GaN _χ As _{1-χ} Using a N Radical as the N Source", Konkow, et al Jpn. J. Appl. Phys. Vo. 3 1994 pp L1056-L1058
AR	"Structural characterization of a dimeric dimethylindium azide and its use as a single-source precursor for InN thin films", Bae, et al J. of Organic Metallic Chemistry 616(2000) 128-134
AS	"Preperation of Phase-Pure InSe Thin Films by MOCVD Using a New Single-Source Precursor [(Me) ₂ In(μ-SeMe)] ₂ , Cho, et al Bull. Korean Chem. Soc. 2003 Vol. 24, No. 5 645-646

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.